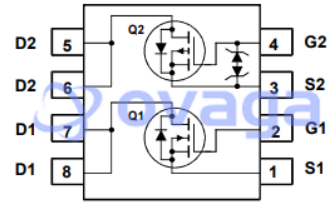


Dual N & P-Channel PowerTrench<sup>®</sup> MOSFET Q1-N-Channel: 30 V, 6.4 A, 26 mΩ Q2-P-Channel: -30 V, -4.5 A, 51 mΩ 1 FDS89 58B Datasheets Search Partnumber : Start with "FDS89 58B " - Total : 38 ( 1/2 Page) NO Part no Electronics Description View Electronic Manufacturer 38 FDS89141 Dual N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 3



Images are for reference only

Manufacturers	<a href="#">ON Semiconductor, LLC</a>
Package/Case	SOP-8
Product Type	Transistors
RoHS	Green
Lifecycle	

Please submit RFQ for FDS8958B or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

These dual N- and P-Channel enhancement mode power field effect transistors are produced using an advanced PowerTrench<sup>®</sup> process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance. These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

## Features

Q1 N-ChannelMax. = 10 V, = 39 mΩ at = 5.2 A

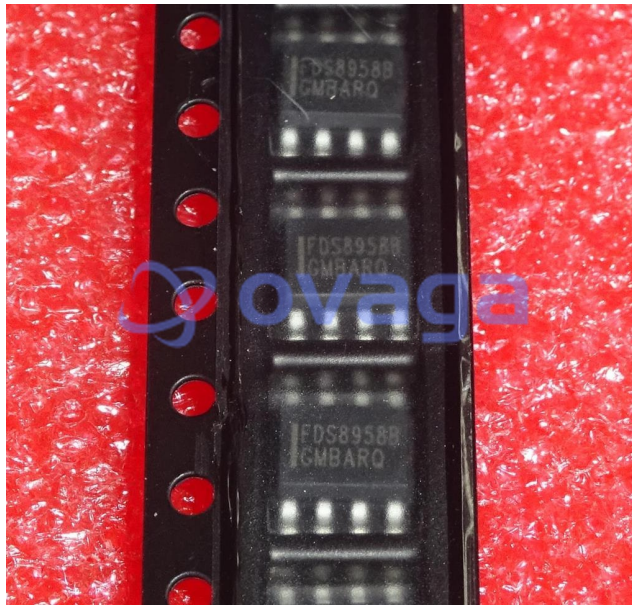
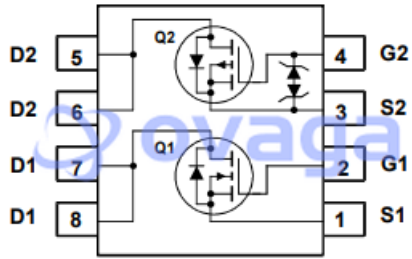
Q2 P-ChannelMax. = -10 V, = 80 mΩ at = -3.3 A

HBM ESD protection level > 3.5 kV

RoHS Compliant

## Application

ONSEMI

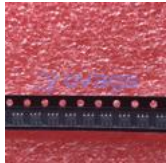


### Related Products



#### [FDC645N](#)

ON Semiconductor, LLC  
SSOT-6



#### [FDC6305N](#)

ON Semiconductor, LLC  
SSOT-6



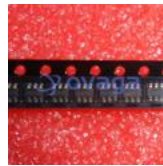
#### [FDD8647L](#)

ON Semiconductor, LLC  
TO-252-3



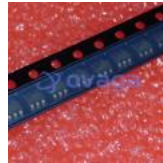
#### [FDD5N50NZTM](#)

ON Semiconductor, LLC  
TO-252



#### [FDC637BNZ](#)

ON Semiconductor, LLC  
SSOT-6



#### [FDC602P](#)

ON Semiconductor, LLC  
SOT163



#### [FDB070AN06A0](#)

ON Semiconductor, LLC  
TO-263



#### [FDD3670](#)

ON Semiconductor, LLC  
TO-252AA